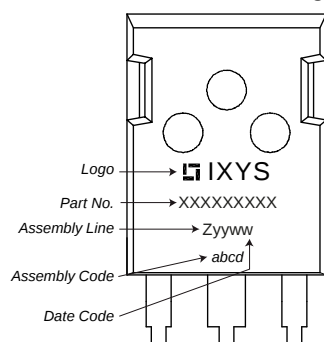


Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_R	reverse current, drain current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			250	μA
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			1	mA
V_F	forward voltage drop	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			2.74	V
		$I_F = 60\text{ A}$				3.27	V
		$I_F = 30\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			1.79	V
		$I_F = 60\text{ A}$				2.30	V
I_{FAV}	average forward current	$T_C = 120^{\circ}\text{C}$ rectangular	$T_{VJ} = 175^{\circ}\text{C}$ d = 0.5			30	A
V_{F0}	threshold voltage	} for power loss calculation only				1.12	V
r_F	slope resistance					16	m Ω
R_{thJC}	thermal resistance junction to case					0.9	K/W
R_{thCH}	thermal resistance case to heatsink				0.25		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				165	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_R = 0\text{ V}$		$T_{VJ} = 45^{\circ}\text{C}$		200	A
C_J	junction capacitance	$V_R = 600\text{ V}$ f = 1 MHz		$T_{VJ} = 25^{\circ}\text{C}$		12	pF
I_{RM}	max. reverse recovery current	} $I_F = 30\text{ A}; V_R = 600\text{ V}$ -di _F /dt = 200 A/ μs		$T_{VJ} = 25^{\circ}\text{C}$		8.5	A
				$T_{VJ} = 100^{\circ}\text{C}$		13	A
t_{rr}	reverse recovery time			$T_{VJ} = 25^{\circ}\text{C}$		60	ns
				$T_{VJ} = 100^{\circ}\text{C}$		170	ns

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ^{a)}			70	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

Product Marking

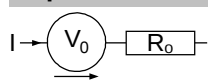


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEC60-12A	DSEC60-12A	Tube	30	476412

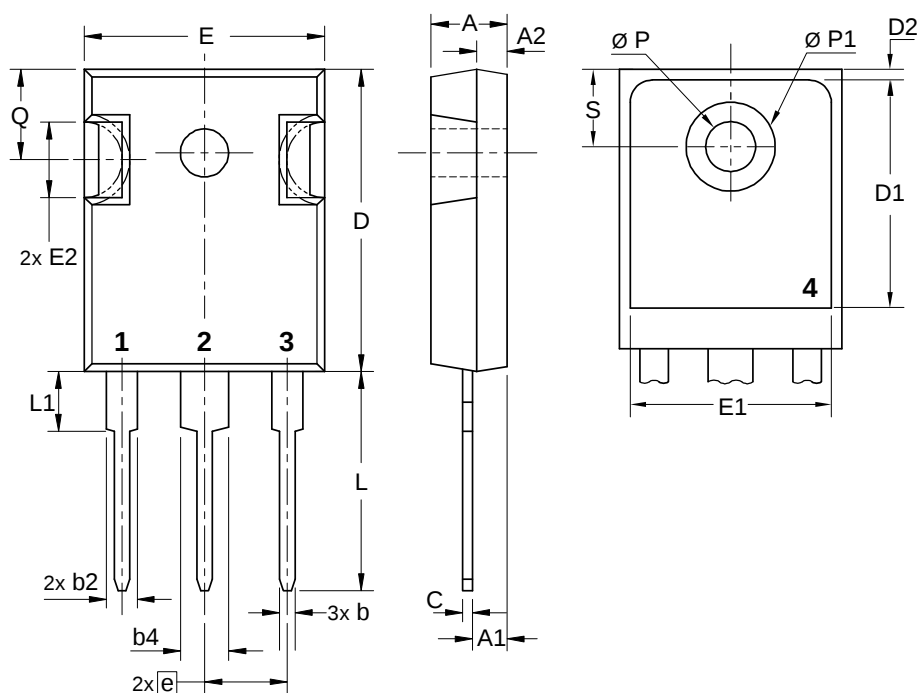
Equivalent Circuits for Simulation

* on die level

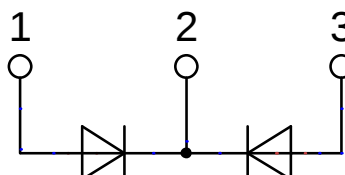
$T_{VJ} = 175\text{ °C}$

			Fast Diode
$V_{0\text{ max}}$	threshold voltage	1.12	V
$R_{0\text{ max}}$	slope resistance *	13.4	mΩ

Outlines TO-247



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215	BSC	5.46	BSC
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242	BSC	6.14	BSC
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



Fast Diode

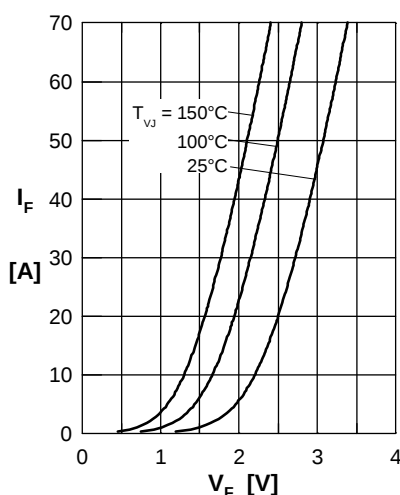


Fig. 1 Forward current I_F versus V_F

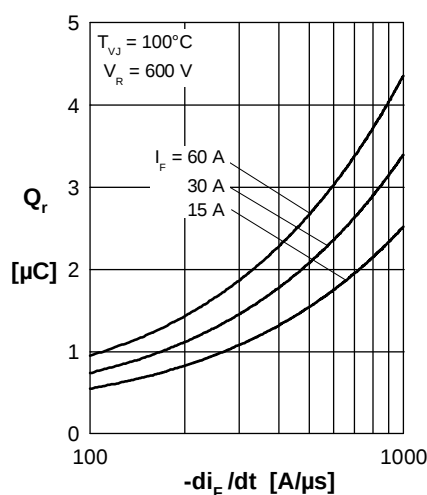


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

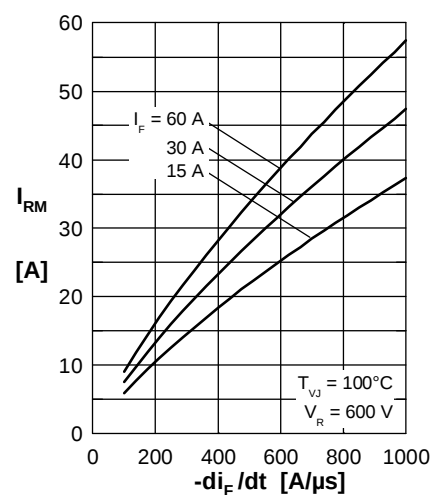


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

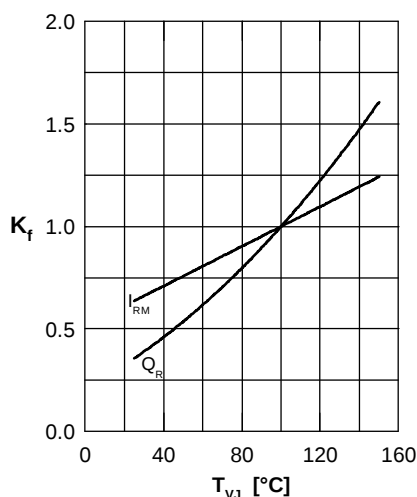


Fig. 4 Typ. dynamic parameters Q_r , I_{RM} versus T_{VJ}

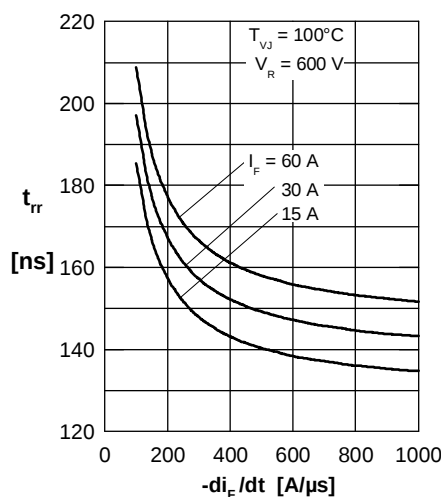


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

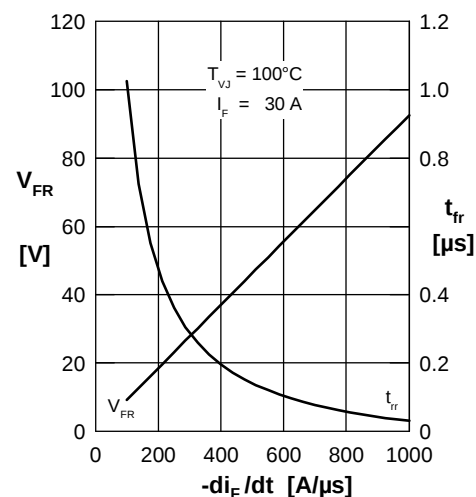


Fig. 6 Typ. peak forward voltage V_{FR} and t_{rr} versus di_F/dt

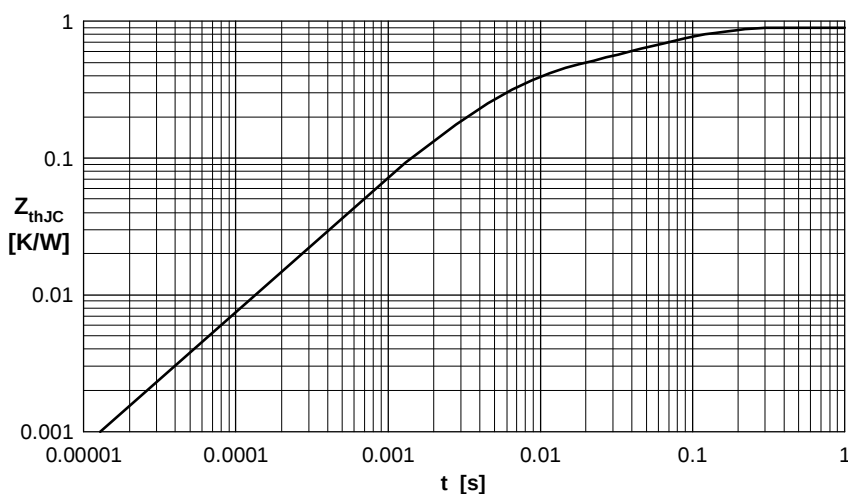


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.030	0.001
2	0.080	0.030
3	0.300	0.006
4	0.490	0.060